

**DESCRIPTION**

This is a high speed Silicon detector optimized for applications requiring high Responsivity and a fast response time.

**FEATURES**

- High Responsivity
- High Electrical Bandwidth/Fast response time
- High Reliability/Hermetic Package

**ABSOLUTE MAXIMUM RATINGS**

- Storage temperature..... -55°C to +125°C
- Case operating temperature..... -40°C to +100°C
- Lead solder temperature..... 260°C, 10 seconds
- Reverse Breakdown Voltage..... 100 Volts

**OUTLINE DIMENSIONS**

Tolerances are +/-0.005 inches, except as noted  
 The case is electrically isolated from the pins.

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Capacitance	Vr = 20 V, f = 1 MHz	C		3.0		pF
Responsivity (50 μm coupled)	H = 10 μW, Vr = 5 Volts 50 μm Core, λ = 850 nm	R <sub>c</sub>	.45	.55		A/W
Dark Current	Vr = 5 Volts, H = 0 mW	I <sub>d</sub>		2	10	nA
Response Time	10%-90%, Vr = 5 Volts R <sub>L</sub> = 50 Ω	t <sub>r</sub>		6.0	10	nsec
		t <sub>f</sub>		6.0	10	nsec
Spectral Response		λ	400		1100	nm
Electrical Bandwidth	Vr = 5 Volts	BWE		50		MHz

**ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)**